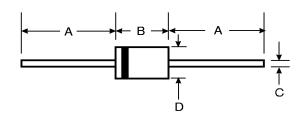


# 1N5820 - 1N5822

### 3.0A SCHOTTKY BARRIER RECTIFIERS

#### **Features**

- Schottky Barrier Chip
- Guard Ring Die Construction for Transient Protection
- Low Power Loss, High Efficiency
- High Surge Capability
- High Current Capability and Low Forward Voltage Drop
- For Use in Low Voltage, High Frequency Inverters, Free Wheeling, and Polarity Protection Application
- Plastic Material UL Flammability Classification 94V-0



DO-201AD					
Dim	Min	Max			
Α	25.40	_			
В	7.20	9.50			
С	1.20	1.30			
D	4.80	5.30			
All Dimensions in mm					

## **Mechanical Data**

Case: Molded Plastic

 Terminals: Plated Leads Solderable per MIL-STD-202, Method 208

Polarity: Cathode Band
Weight: 0.3 grams (approx)
Mounting Position: Any

Marking: Type Number

# Maximum Ratings and Electrical Characteristics @ TA = 25°C unless otherwise specified

Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Characteristic	Symbol	1N5820	1N5821	1N5822	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V <sub>RRM</sub> V <sub>R</sub> WM V <sub>R</sub>	20	30	40	V
RMS Reverse Voltage	V <sub>R(RMS)</sub>	14	21	28	V
Average Rectified Output Current (Note 1) @ T <sub>L</sub> = 90°C	lo	3.0		А	
Non-Repetitive Peak Forward Surge Current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method) @ T <sub>L</sub> = 75°C	I <sub>FSM</sub>	80		А	
Forward Voltage $@I_F = 3.0A$ $@I_F = 9.4A$	V <sub>FM</sub>	0.475 0.850	0.500 0.900	0.525 0.950	V
	I <sub>RM</sub>	2.0 20		mA	
Typical Junction Capacitance (Note 2)	Cj	250			pF
Typical Thermal Resistance Junction to Ambient	R <sub>0JA</sub>	20			K/W
Operating and Storage Temperature Range	T <sub>j,</sub> T <sub>STG</sub>	-65 to +150			°C

Notes:

- 1. Measured at ambient temperature at a distance of 9.5mm from the case.
- 2. Measured at 1.0 MHz and applied reverse voltage of 4.0V DC.

DS23003 Rev. D 1 of 2 1N5820-1N5822

